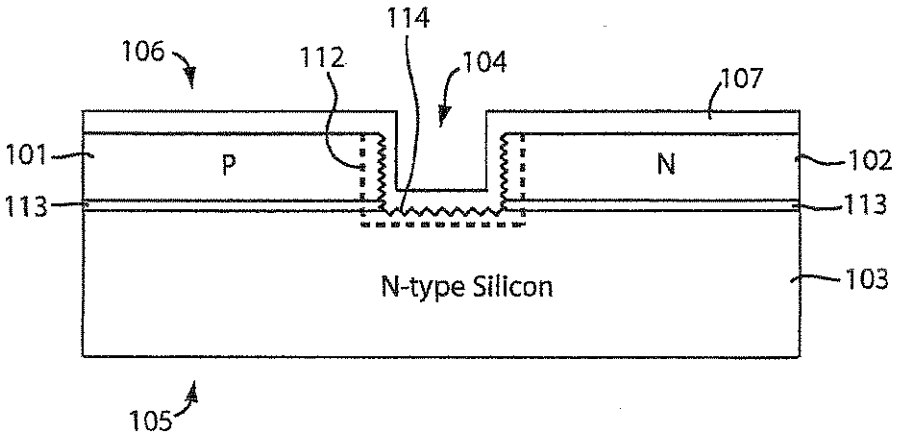

114
106
112
104
107
101
P
N
102
113
113
N-type Silicon
103
105

FIG. 1

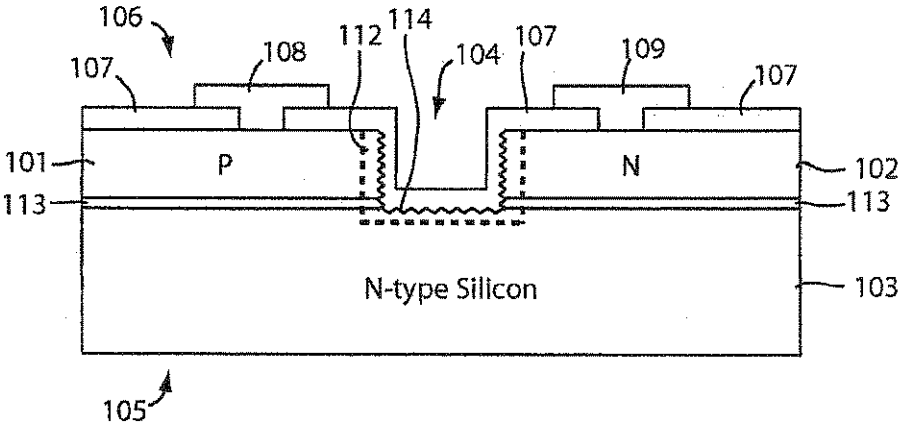

106
114
107
108
112
104
107
109
107
101
P
N
102
113
113
N-type Silicon
103
105

FIG. 2

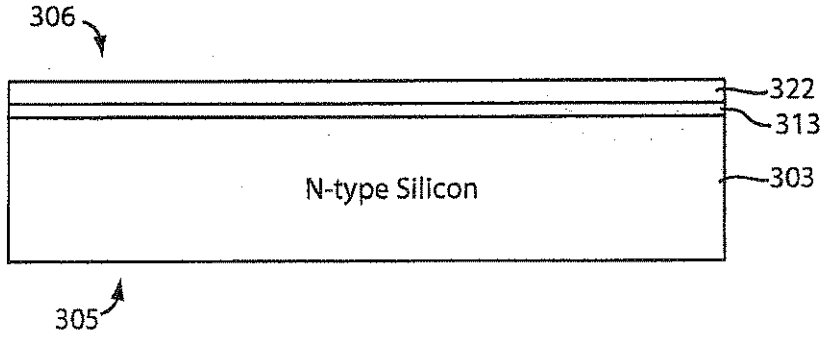


FIG. 3

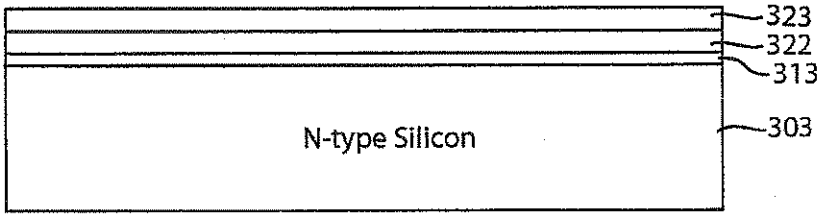


FIG. 4

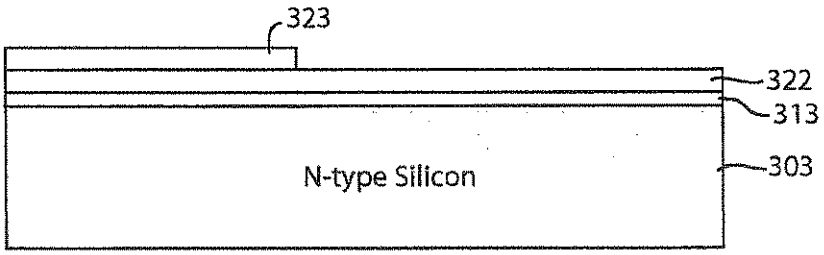


FIG. 5

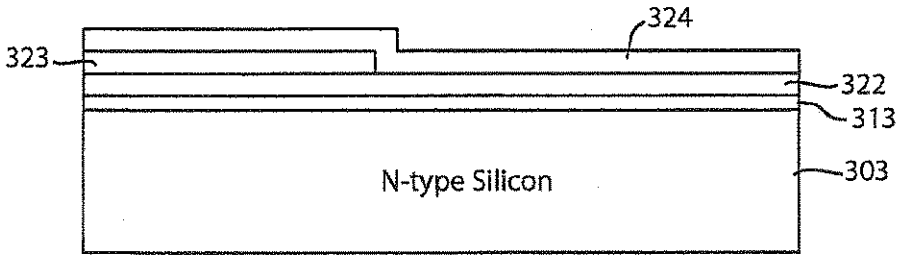


FIG. 6

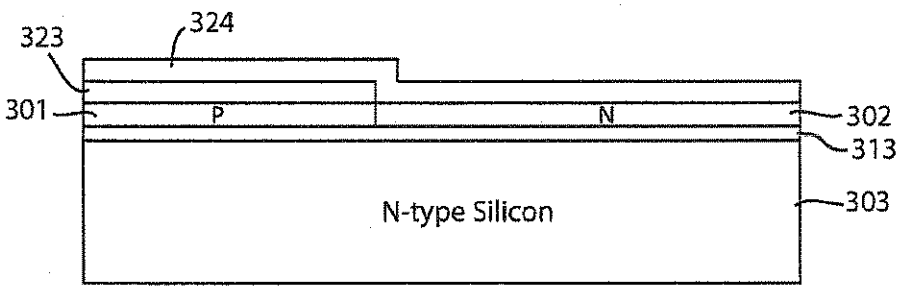


FIG. 7A

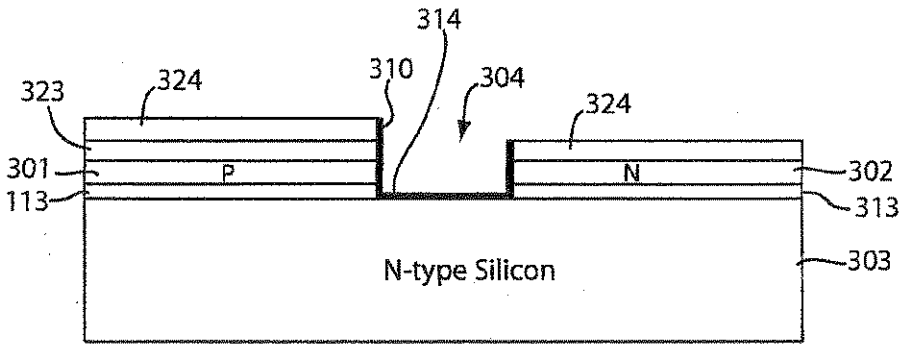


FIG. 8A

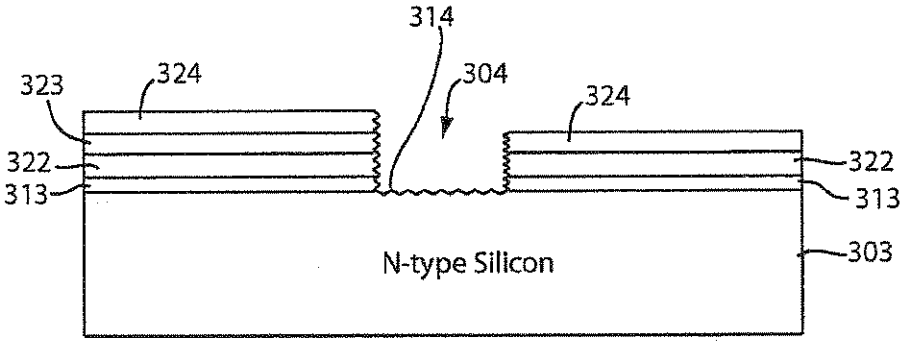

314
323
324
304
324
322
322
313
313
N-type Silicon
303

FIG. 7B

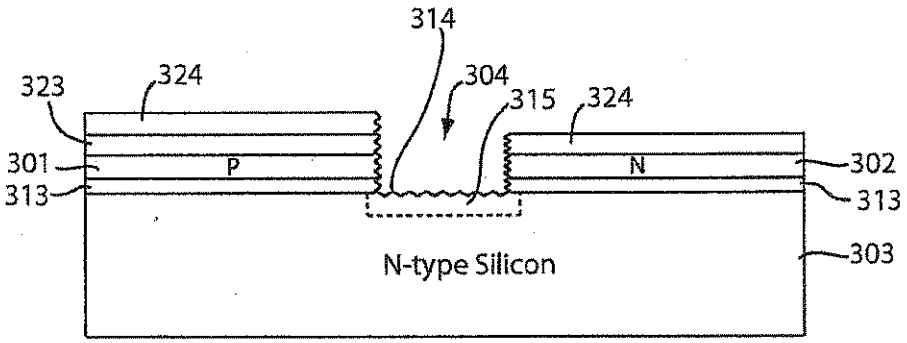

314
323
324
304
315
324
301
P
N
302
313
313
N-type Silicon
303

FIG. 8B

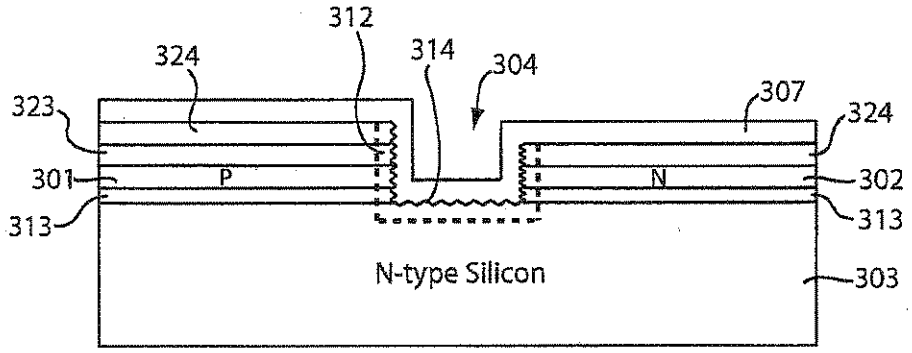

312
324
314
304
323
307
324
301
P
N
302
313
313
N-type Silicon
303

FIG. 9

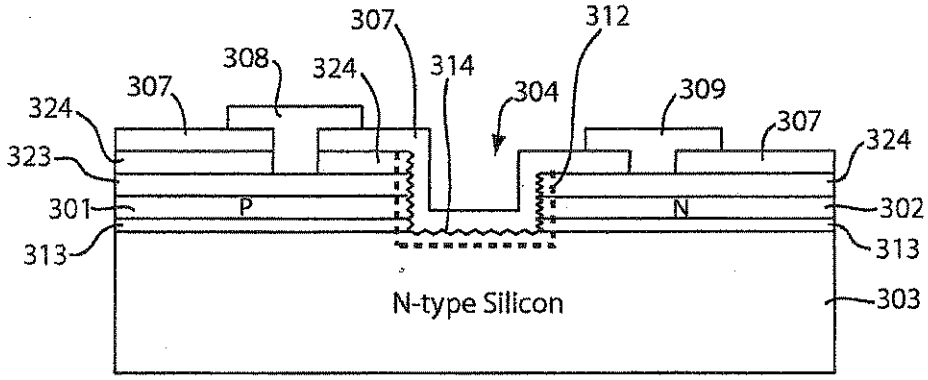

307
312
308
324
314
307
304
309
324
307
324
323
301
P
N
302
313
313
N-type Silicon
303

FIG. 10

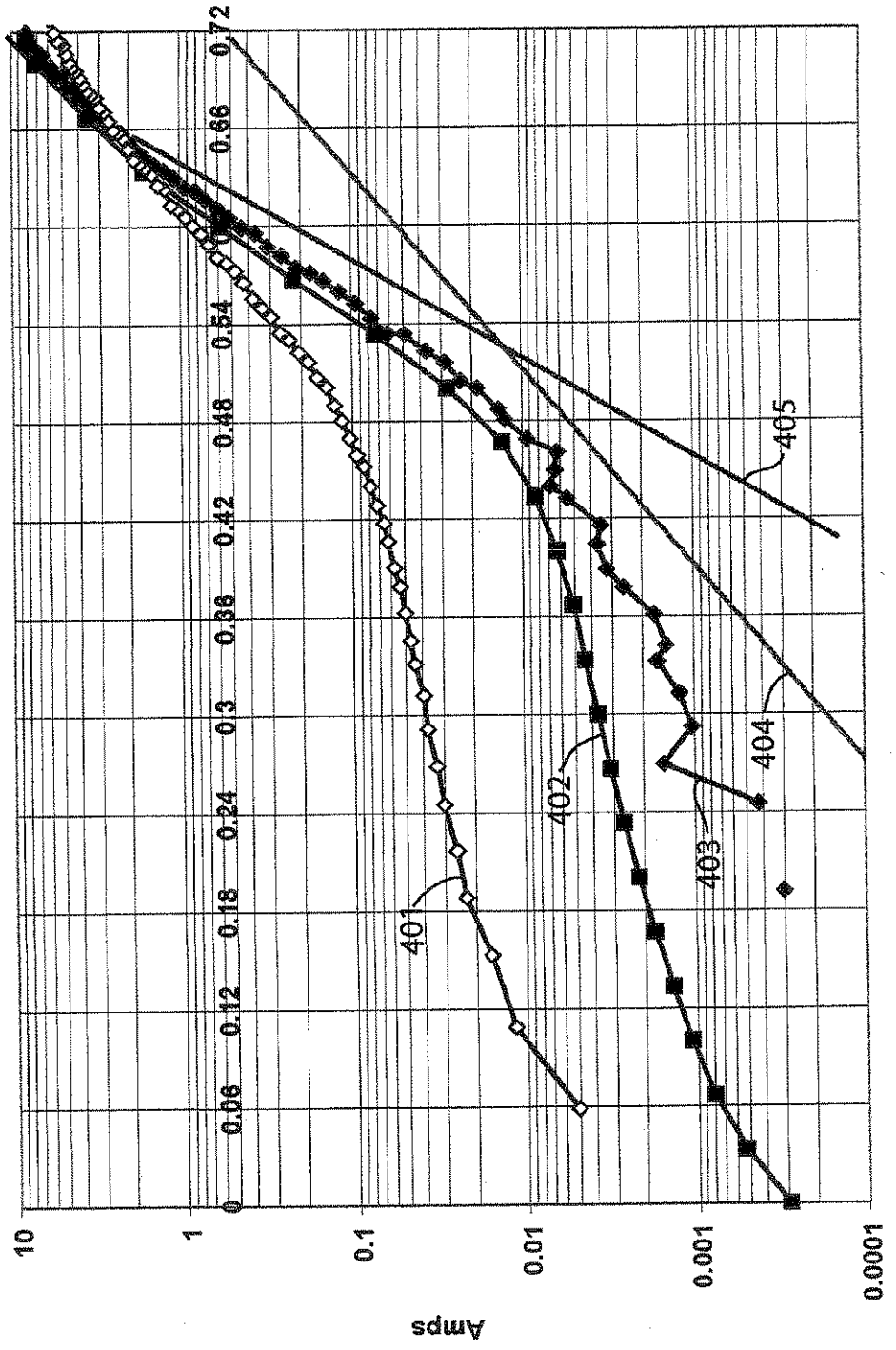

Amps
10
1
0.1
0.01
0.001
0.0001
Volts
0
0.06
0.12
0.18
0.24
0.3
0.36
0.42
0.48
0.54
0.66
0.72
401
402
403
404
405

FIG. 11

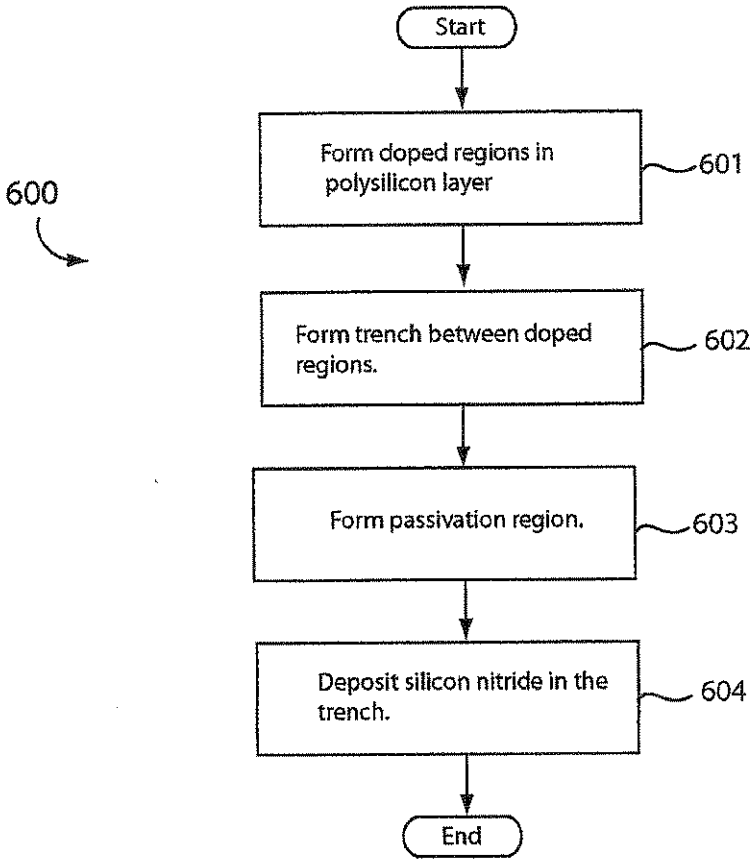

600
Start
Form doped regions in polysilicon layer
601
Form trench between doped regions.
602
Form passivation region.
603
Deposit silicon nitride in the trench.
604
End

FIG. 12